Thin film filter STBP218-1R6-K806

COM-MW TECHNOLOGY

Bandwidth21.0-22.6GHz, Rejection40@DC-19.2GHz, 40@24.1-36.0GHz

Product features

High precision machining technology

Low temperature drift, high power.

Ceramic substrate, 50 Ω coplanar waveguide

Gold wire bonding

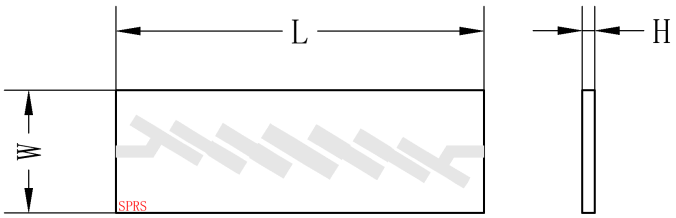
Tech specifications

Items	Parameters	Units
Center Frequency	21.8	GHz
Bandwidth	21.0-22.6	GHz
Center loss	2.4	dB
Ripple	1.0	dB
VSWR	1.7:1	
Group delay ripple	0.4	ns
Rejection	40@DC-19.2GHz	dBc
Rejection	40@24.1-36.0GHz	dBc

Other requirement (Design assurance)

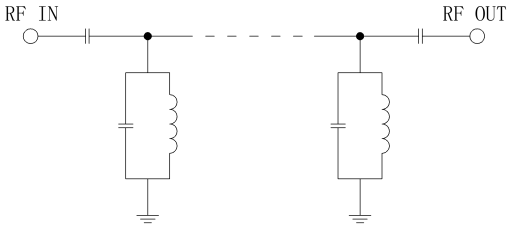
power	2W CW
Operation Temp.	-55~+85°C
Storage Temp.	-55~+125°C
Outline size	L:8.5，W:3.0，h:0.26

Outline drawing: Port centered

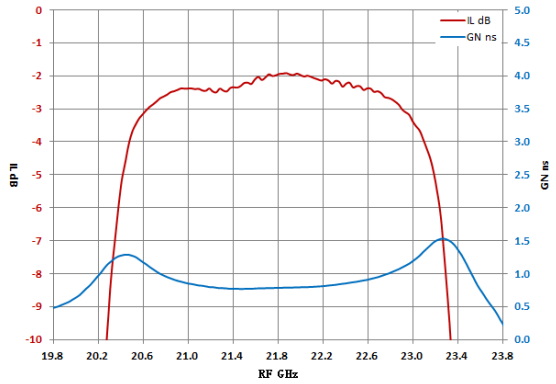


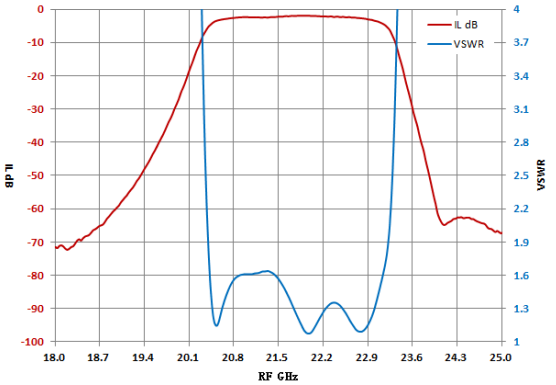
Reference picture

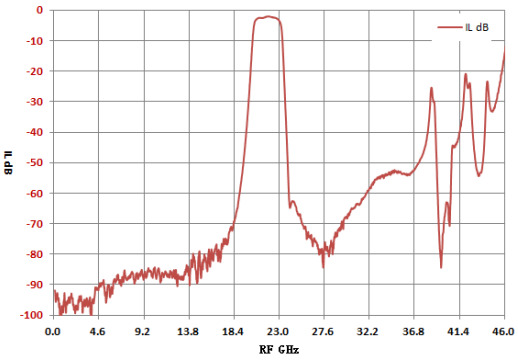
Schematic diagram



Typical test curve

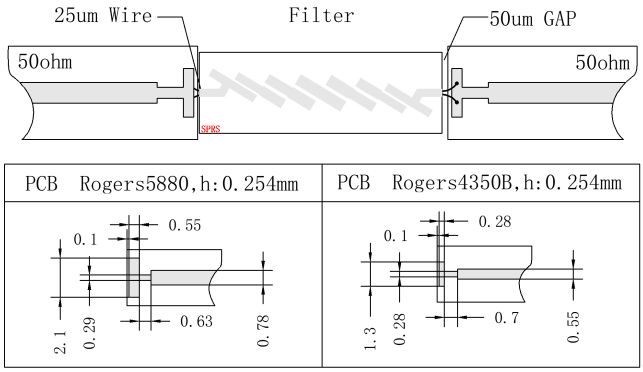






Note: The specifications and performance data contained in this data sheet are based on tests established by CMW.

Suggested PCB Layout



Note

1: 0.1mm from the side wall, 1.75mm from the surface to the upper cover.

2: Suggest using conductive adhesive for bonding;

3: The chip should be installed on materials such as Kovar (recommended) or copper with a thermal expansion coefficient similar to that of ceramics (6.7ppm/C), and the carrier thickness should be ⩾ 0.2mm;

4: Suggest using a T-shaped structure for microstrip bonding.

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